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INTERNATIONAL PRELIMINARY EXAMINATION REPORT

(PCT Artcle 36 and Rule 70)

Applicant's or agent's file reference FGPE03-001	FOR FURTHER ACTION					
International application No.	International filing date(day/mo	nth/year) Priority date (day	/month/year)			
PCT/KR2003/001668	19 AUGUST 2003 (19.0	3.2003) 19 AUGUST 20	02 (19.08.2002)			
international Patent Classification (IPC	C) or national classification and IP					
Applicant						
LG INNOTEK CO.,LTD et :	al .		****			
and is transmitted to the applica	nt according to Article 36.	red by this International Prelimina	ry Examining Authority			
2. This REPORT consists of a tota	of 3 sheets, inclu	ling this cover sheet.				
This report is also accompanied by ANNEXES, i.e., sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications made before this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions under the PCT).						
These annexes consist of a total ofsheets.						
3. This report contains indications relating to the following items:						
I X Basis of the report	t					
II Priority						
III Non-establishmen	t of opinion with regard to novelty	, inventive step and industrial applic	ability			
IV Lack of unity of in	nvention					
V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement						
VI Certain document	s cited					
VII Certain defects in	the international application					
VIII Certain observations on the international application						
Date of submission of the demand	Date	of completion of this report				
05 DECEMBER 200	3 (05.12.2003)	06 DECEMBER 2004 (06.12.	2004)			
Name and mailing address of the IPE		norized officer	A MAN			
Korean Intellectual Property Office 920 Dunsan-dong, Seo-gu, Daejeon 302-701, Republic of Korea		KIM, Dong Yup				
Facsimile No. 82-42-472-7140	Tele	phone No. 82-42-481-5749	A STATE OF THE PARTY OF THE PAR			

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International aplication No.

PCT/KR2003/001668

I.	Basis	of the report				
1.	With	regard to the elements of the international application:*				
	X	the international application as originally filed				
		the description:	, as originally filed			
		pagespages	, as originally filed , filed with the demand			
		pages, filed with the letter of				
		the claims:	as prisingll. Flad			
		pages , as amended (together with any	_ , as originally filed y statment) under Article 19			
		pages	, filed with the demand			
	, -	pages, filed with the letter of				
		the drawings: pages	_ , as originally filed			
		pages	, filed with the demand			
		pages, filed with the letter of				
		the sequence listing part of the description:	, as originally filed			
		pages	, filed with the demand			
		pages, filed with the letter of				
2.	the i	With regard to the language, all the elements marked above were available or furnished to this Authority in the language in which he international application was filed, unless otherwise indicated under this item. These elements were available or furnished to this Authority in the following language English which is the language of a translation furnished for the purposes of international search (under Rule 23.1(b)). The language of publication of the international application (under Rule 48.3(b)).				
		the language of the translation furnished for the purposes of international preliminary examination or 55.3).	ination(under Rules 55.2 and/			
3		ith regard to any nucleotide and/or amino acid sequence disclosed in the international application, the international eliminary examination was carried out on the basis of the sequence listing: contained inthe international application in written form.				
	닏	filed together with the international application in computer readable form. furnished subsequently to this Authority in written form.				
		furnished subsequently to this Authority in computer readable form				
	<u> </u>	The statement that the subsequently furnished written sequence listing does not go be	yond the disc losure in the			
		international applicationas as filed has been furinshed. The statement that the information recorded in computer readable form is identical to the been furnished.				
4.		The amendments have resulted in the cancellation of:				
		the description, pages				
		the claims, Nos.				
		the drawings, sheets				
5.		This report has been established as if (some of) the amendments had not been made, sing go beyond the disclosure as filed, as indicated in the Supplemental Box(Rule 70.2(c)).**	ce they have been considered to			
*	in th	lacement sheets which have been furnished to the receiving Office in response to an invitation w his opinion as "originally filed." and are not annexed to this report since they do not contain 70.17).	nder Article 14 are referred to 1 amendments (Rules 70.16			
	** Any replacement sheet containing such amendments must be referred to under item I and annexed to this report.					

INTERNATIONAL PRELIMINARY EXAMINATION

International aplication No.
PCT/KR2003/001668

/. Reasoned statement under Article 35(2) with regard to novelty, inventive step o	or industrial applicability;
citations and explanations supporting such statement	

1.	Statement			
	Novelty (N)	Claims	1-5, 10-20	YES
1	torony (11)	Claims	6-9	NO
	Inventive step (IS)	Claims	1-5, 10-20	YES
1		Claims	6-9	NO
	Industrial applicability (IA)	Claims	1-20	YES
	,	Claims	NONE	_ <u>N</u> O

2. Citations and explanations (Rule 70.7)

1) Documents cited in the International Search Report:

D1 : JP 9-153643 A

D2 : JP 9-129925 A

D3: JP 2001-7397 A

D4 : JP 10-173220 A

D5 : JP 7-302929 A

D6 : JP 7-254733 A

2) The subject-matter of claims 6-9 lacks novelty (Article 33(2) PCT).

The subject-matter of claims 6-9 is a nitride semiconductor LED comprising: a substrate; a GaN-based buffer layer; a first electrode layer of a n+-GaN layer; n-GaN layer formed on the first electrode layer; an active layer; and a second electrode layer of a p-GaN layer formed on the active layer.

But D1 discloses a nitride semiconductor having the same structure as claims 6-9 of the present invention. An LED, described in paragraph 0010-0012 and figure 1 of D1, comprises a substrate; a buffer layer; a first electrode layer of a highly doped n-GaN layer formed on the first electrode layer; an active layer; and a second electrode layer of a p-GaN layer formed on the active layer.

Although there is a slight difference in the material of the buffer layer, it is a well-known fact that the AlN buffer can be easily substituted for the GaN-based buffer.

Therefore, the subject-matter of claims 6-9 is not inventive.

3) The present application is believed to be industrially applicable according to PCT Article 33(4).